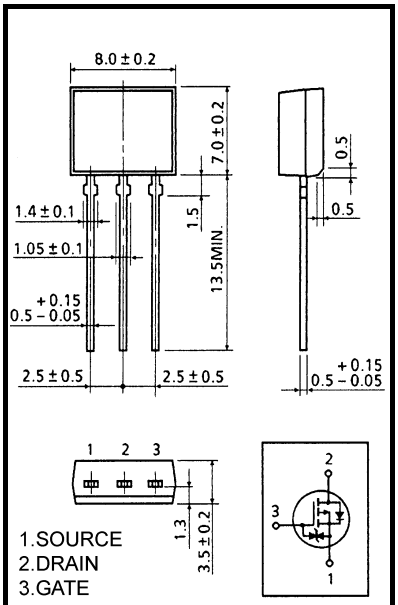
TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (U−MOS III)

2SJ669

Relay Drive, DC/DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON-resistance: $R_{DS\ (ON)}$ = 0.12 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 5.0 S (typ.)
- Low leakage current: I_{DSS} = −100 μA (max) (V_{DS} = −60 V)
- Enhancement mode: V_{th} = −0.8 to −2.0 V
  (V_{DS} = −10 V, I_D = −1 mA)

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-8M1B

Weight: 0.54 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Drain−source voltage		V_{DSS}	−60	V
Drain−gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	−60	V
Gate−source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	−5	A
	Pulse (Note 1)	I_{DP}	−20	A
Drain power dissipation		P_D	1.2	W
Single-pulse avalanche energy (Note 2)		E_{AS}	40.5	mJ
Avalanche current		I_{AR}	−5	A
Repetitive avalanche energy (Note 3)		E_{AR}	0.12	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	104	°C / W

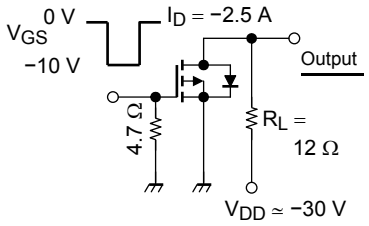
Note 1: The channel temperature should not exceed 150℃ during use.

Note 2: V_{DD} = −25 V, T_{ch} = 25°C (initial), L = 2.2 mH, R_G = 25 Ω, I_{AR} = −5 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

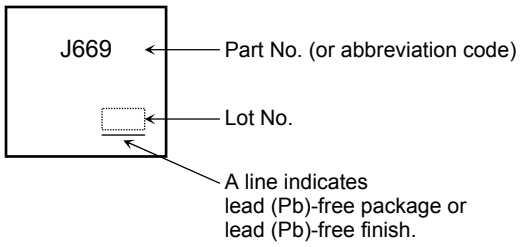
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cutoff current		I_{DSS}	V_{DS} = −60 V, V_{GS} = 0 V	—	—	−100	μA
Drain−source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −10 mA, V_{GS} = 0 V	−60	—	—	V
		$V_{(BR)\ DSX}$	I_D = −10 mA, V_{GS} = 20 V	−35	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = −10 V, I_D = −1 mA	−0.8	—	−2.0	V
Drain−source ON-resistance		$R_{DS\ (ON)}$	V_{GS} = −4 V, I_D = −2.5 A	—	0.16	0.25	Ω
			V_{GS} = −10 V, I_D = −2.5 A	—	0.12	0.17	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −2.5 A	2.5	5.0	—	S
Input capacitance		C_{iss}	V_{DS} = −10 V, V_{GS} = 0 V, f = 1 MHz	—	700	—	pF
Reverse transfer capacitance		C_{rss}		—	60	—	
Output capacitance		C_{oss}		—	90	—	
Switching time	Rise time	t_r	 Duty ≦ 1%, t_w = 10 μs	—	14	—	ns
	Turn−on time	t_{on}		—	24	—	
	Fall time	t_f		—	14	—	
	Turn−off time	t_{off}		—	95	—	
Total gate charge (gate−source plus gate−drain)		Q_g	V_{DD} ≈ −48 V, V_{GS} = −10 V, I_D = −5 A	—	15	—	nC
Gate−source charge		Q_{gs}		—	11	—	
Gate−drain (“Miller”) charge		Q_{gd}		—	4	—	

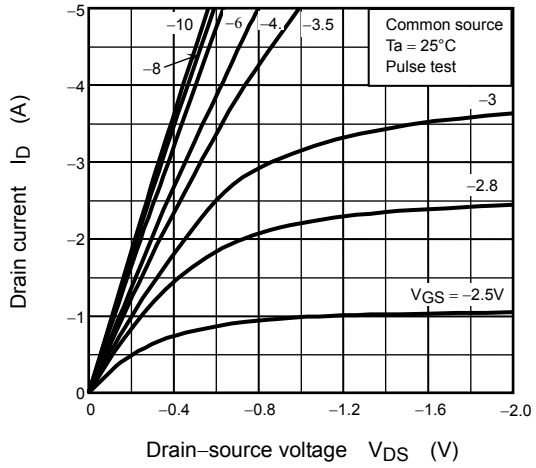
Source−Drain Ratings and Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	−5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	−20	A
Forward voltage (diode)	V_{DSF}	I_{DR} = −5 A, V_{GS} = 0 V	—	—	1.7	V
Reverse recovery time	t_{rr}	I_{DR} = −5 A, V_{GS} = 0 V dI_{DR} / dt = 50 A / μS	—	40	—	ns
Reverse recovery charge	Qrr		—	32	—	nC

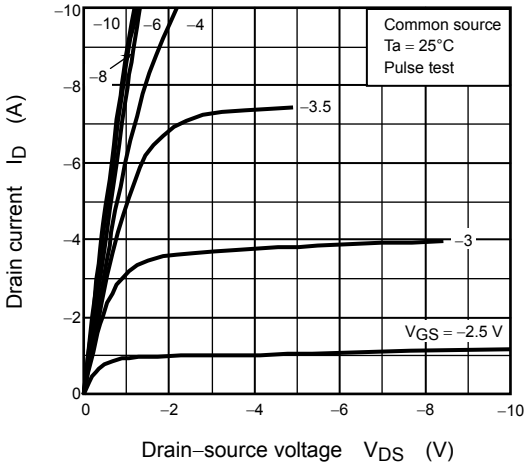
Marking



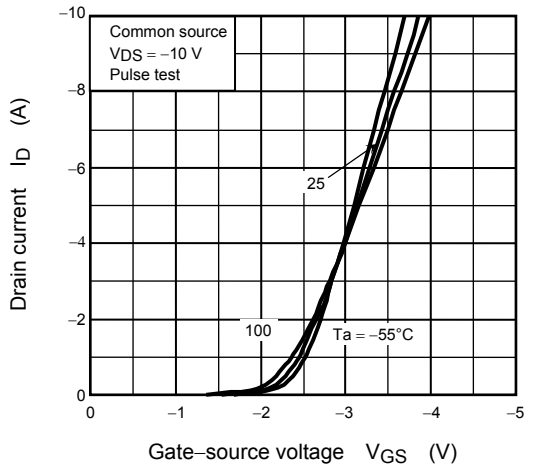
$I_D - V_{DS}$



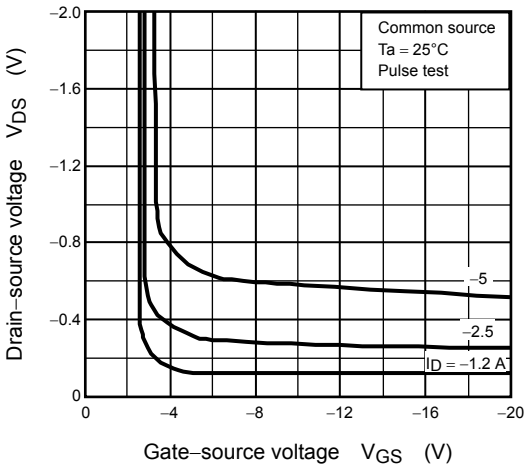
$I_D - V_{DS}$



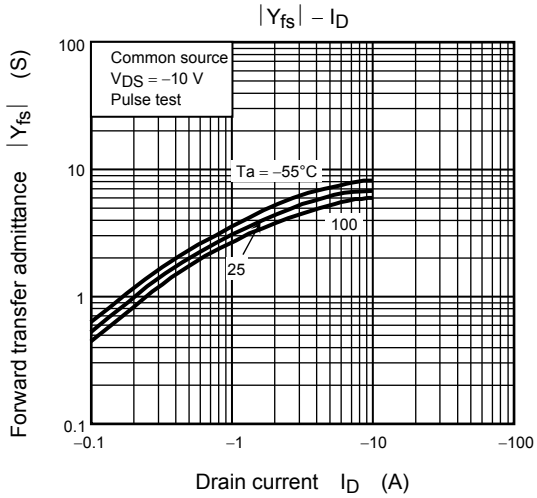
$I_D - V_{GS}$



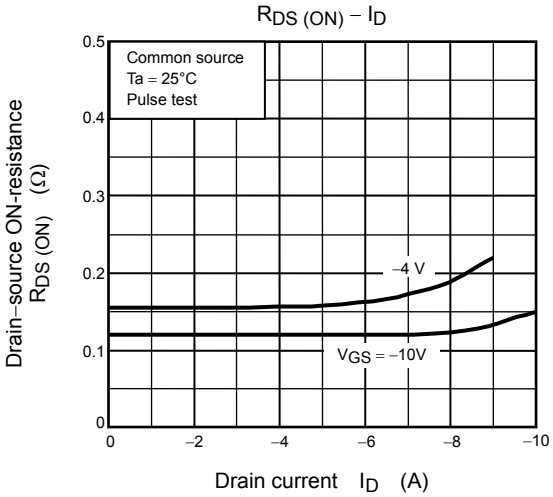
$V_{DS} - V_{GS}$



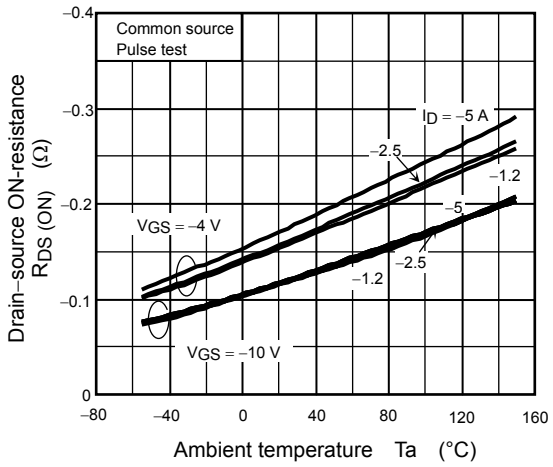
$|Y_{fs}| - I_D$



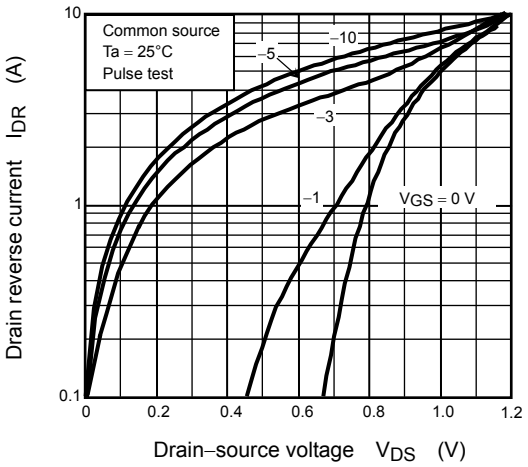
$R_{DS\ (ON)} - I_D$



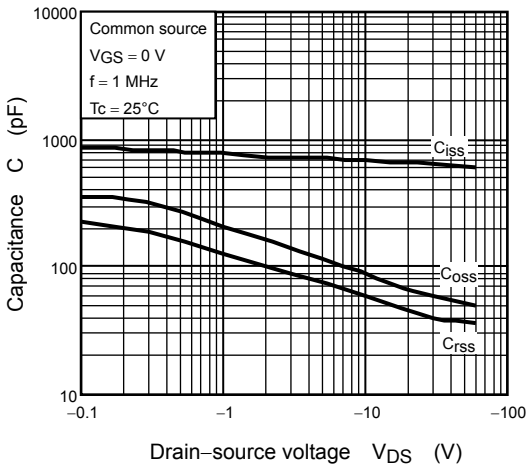
$R_{DS\ (ON)}$ – Ta



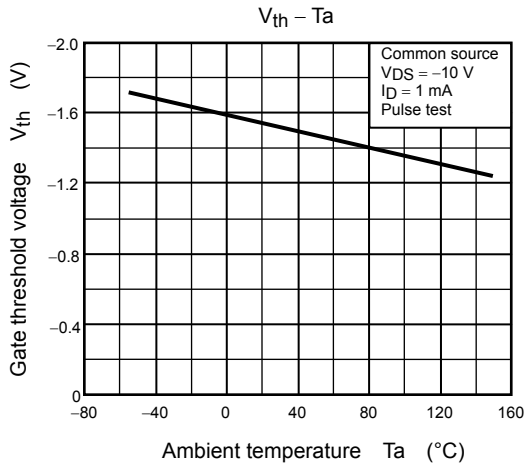
I_{DR} – V_{DS}



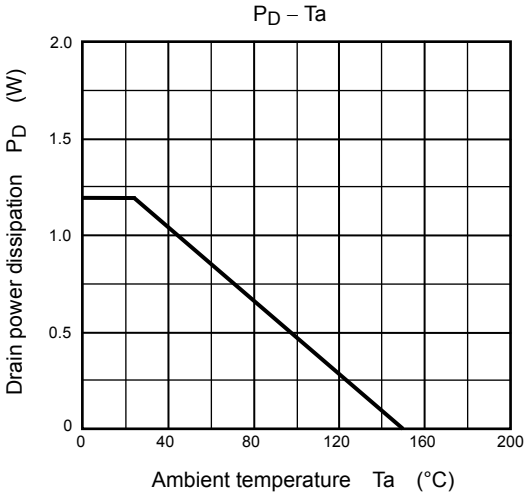
Capacitance – V_{DS}



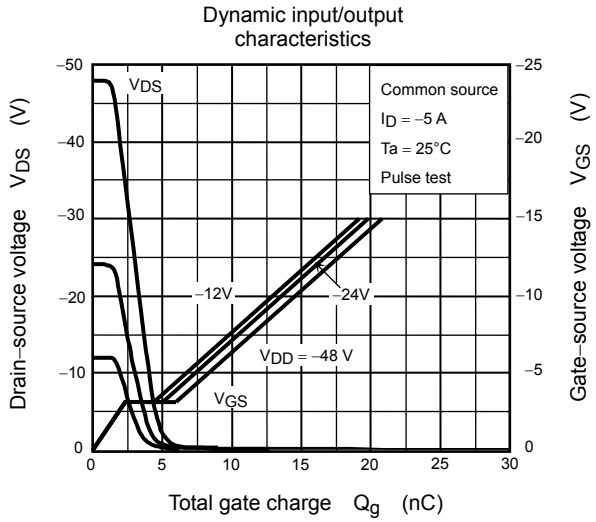
V_{th} – Ta



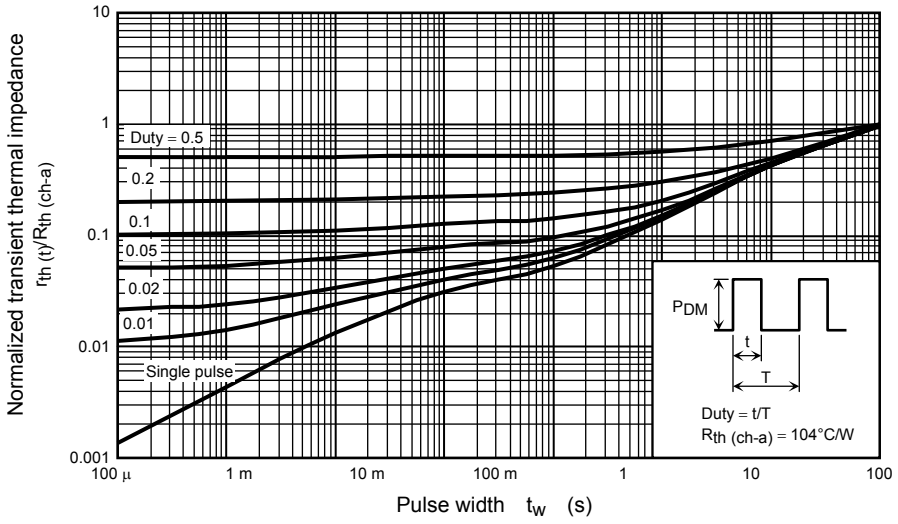
P_D – Ta



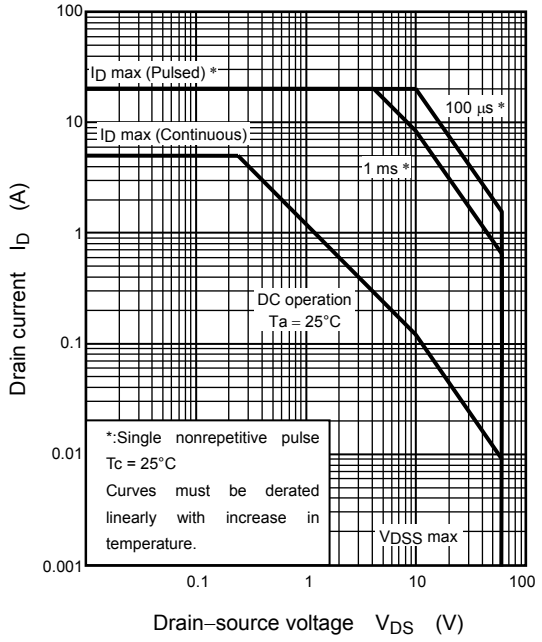
Dynamic input/output characteristics



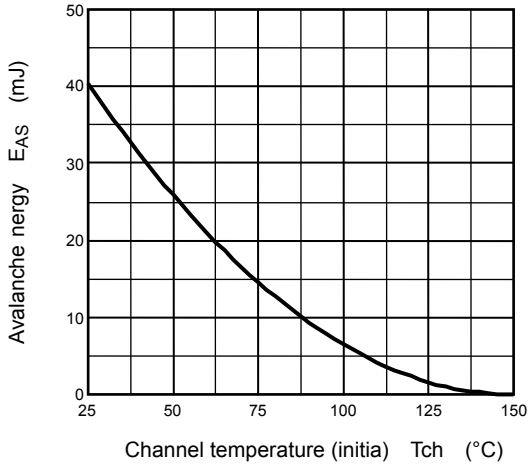
$r_{th} - t_w$

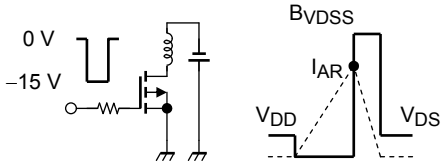


Safe operating area



$E_{AS} - T_{ch}$





Test circuit Waveform

$R_G = 25\ \Omega$
$V_{DD} = -25$ V, L = 2.2 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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20070701-EN

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